MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data speet

SMF15CT1G







Applications

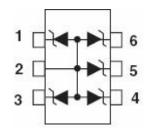
- · Cellular handsets and accessories
- Portable electronics
- · Computers and peripherals
- Communications systems
- · Audio and video equipment.



SOT-363

Features

- Uni-directional ESD protection of up to fivelines
- Bi-directional ESD protection of up to four lines
- Low diode capacitance
- · Low clamping voltage
- · low leakage current
- IEC 61000-4-2; level 4 (ESD)
- IEC61000-4-5 (surge)
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



Electrical Characteristics								
V _B		BR			I _{PP}	V _{CL} (Max)		С
P/N	Min.	Max.	V _{RM}	I _R	8/20 μs pulse; notes1and2	@ I _{PP} =1A	@ I _{PP} =5A	f=1MHz; $V_R = 0 V$; seeFig.4
	٧	٧	V	μ Α	Α	V	V	pF
SMF15CT1G	17	19	15	1	5	23	29	15

Notes

- 1. Non-repetitive current pulse 8/20 μs exponentially decaying waveform; see Fig.1.
- 2. Measured from any of pins 1, 3, 4, 5 or 6 to pin 2.

Absolute Ratings (T_{amb}=25°C)

Symbol	Parameter	Value	Units
P _{PP}	Peak Pulse Power (t _p = 8/20μs)	150	W
TL	Maximum lead temperature for soldering during 10s	260	°C
T _{stg}	Storage Temperature Range	-60 to +150	°C
T _{op}	Operating Temperature Range	-60 to +150	°C
Tj	Maximum junction temperature	150	°C
V_{PP}	Electrostatic discharge		
	IEC61000-4-2 (contact discharge)	8	kV
	IEC61000-4-2 (air discharge)	15	kV





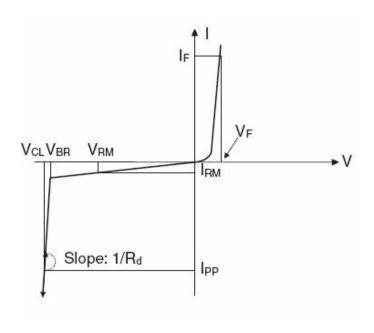


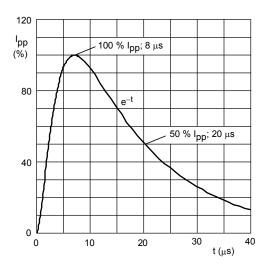




Electrical Parameter

Symbol	Parameter		
V_{RM}	Stand-off voltage		
V_{BR}	Breakdown voltage		
V _{CL}	Clamping voltage		
I _R	Leakage current		
I _{PP}	Peak pulse current		
С	Capacitance		





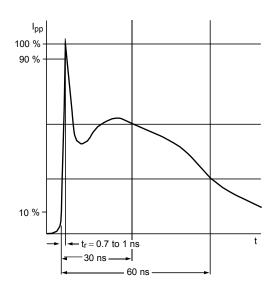
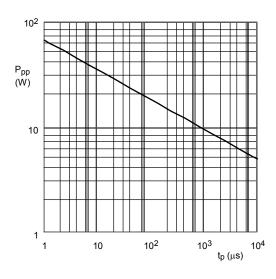


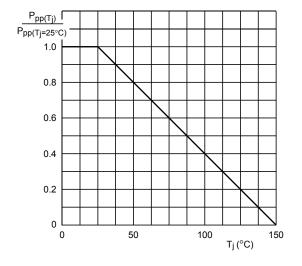
Fig.1 8/20 μs pulse waveform according to IEC 61000-4-5.

Fig.2 Electrostatic Discharge (ESD) pulse waveform according to IEC61000-4-2.



GRAPHICAL DATA

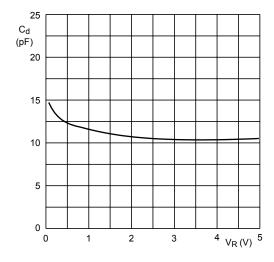


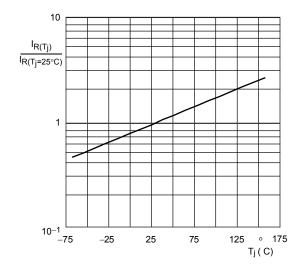


T_{amb} = 25 °C. I_{pp} = 8/20 μs exponentially decaying waveform; see Fig.1.

Fig.3 Peak pulse power dissipation as a function of pulse time; typical values.

Relative variation of peak pulse power as a function of junction temperature; typical values.





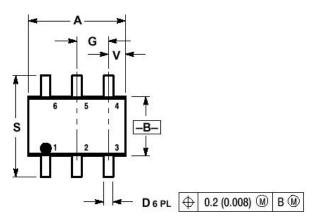
f = 1 MHz; $T_{amb} = 25 \, ^{\circ}\text{C}$.

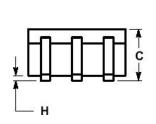
Fig.5 Diode capacitance as af unction of reverse voltage; typical values.

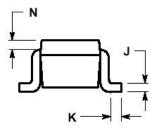
Relative variation of reverse leakage current as a function of junction temperature; typical values.



PACKAGE DIMENSIONS SOT-363







NOTES:

- 1. DIMENSIONINGANDTOLERANCINGPERANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.02	6BSC	0.65BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008	REF	0.20 REF		
S	0.079	0.087	2.00	2.20	
V	0.012	0.016	0.30	0.40	

REEL SPECIFICATION

P/N	PKG	QTY
SMF15CT1G	SOT-363	3000



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